

BC546B, BC547A, B, C, BC548B, C

Amplifier Transistors

NPN Silicon

Features

- Pb-Free Packages are Available*

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector - Emitter Voltage	BC546	65	Vdc
	BC547	45	
	BC548	30	
Collector - Base Voltage	BC546	80	Vdc
	BC547	50	
	BC548	30	
Emitter - Base Voltage	V_{EBO}	6.0	Vdc
Collector Current - Continuous	I_C	100	mAdc
Total Device Dissipation @ $T_A = 25^\circ\text{C}$ Derate above 25°C	P_D	625	mW
		5.0	mW/ $^\circ\text{C}$
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	1.5	W
		12	mW/ $^\circ\text{C}$
Operating and Storage Junction Temperature Range	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction-to-Ambient	$R_{\theta JA}$	200	$^\circ\text{C}/\text{W}$
Thermal Resistance, Junction-to-Case	$R_{\theta JC}$	83.3	$^\circ\text{C}/\text{W}$

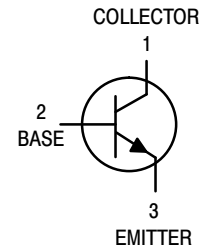
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

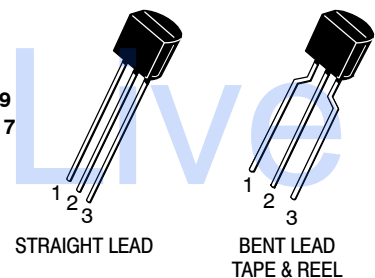


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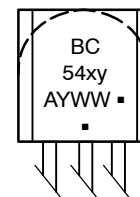
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TO-92
CASE 29
STYLE 17



MARKING DIAGRAM



- x = 6, 7, or 8
- y = A, B or C
- A = Assembly Location
- Y = Year
- WW = Work Week
- = Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 5 of this data sheet.

BC546B, BC547A, B, C, BC548B, C

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
OFF CHARACTERISTICS					
Collector – Emitter Breakdown Voltage (I _C = 1.0 mA, I _B = 0)	V _{(BR)CEO}	65 45 30	– – –	– – –	V
Collector – Base Breakdown Voltage (I _C = 100 μA)	V _{(BR)CBO}	80 50 30	– – –	– – –	V
Emitter – Base Breakdown Voltage (I _E = 10 μA, I _C = 0)	V _{(BR)EBO}	6.0 6.0 6.0	– – –	– – –	V
Collector Cutoff Current (V _{CE} = 70 V, V _{BE} = 0) (V _{CE} = 50 V, V _{BE} = 0) (V _{CE} = 35 V, V _{BE} = 0) (V _{CE} = 30 V, T _A = 125°C)	I _{CES}	– – – –	0.2 0.2 0.2 –	15 15 15 4.0	nA μA
ON CHARACTERISTICS					
DC Current Gain (I _C = 10 μA, V _{CE} = 5.0 V)	h _{FE}	– – –	90 150 270	– – –	–
(I _C = 2.0 mA, V _{CE} = 5.0 V)		110 110 110 110 200 420	– – – 180 290 520	450 800 800 220 450 800	
(I _C = 100 mA, V _{CE} = 5.0 V)		– – –	120 180 300	– – –	
Collector – Emitter Saturation Voltage (I _C = 10 mA, I _B = 0.5 mA) (I _C = 100 mA, I _B = 5.0 mA) (I _C = 10 mA, I _B = See Note 1)	V _{CE(sat)}	– – –	0.09 0.2 0.3	0.25 0.6 0.6	V
Base – Emitter Saturation Voltage (I _C = 10 mA, I _B = 0.5 mA)	V _{BE(sat)}	–	0.7	–	V
Base – Emitter On Voltage (I _C = 2.0 mA, V _{CE} = 5.0 V) (I _C = 10 mA, V _{CE} = 5.0 V)	V _{BE(on)}	0.55 –	– –	0.7 0.77	V
SMALL-SIGNAL CHARACTERISTICS					
Current – Gain – Bandwidth Product (I _C = 10 mA, V _{CE} = 5.0 V, f = 100 MHz)	f _T	150 150 150	300 300 300	– – –	MHz
Output Capacitance (V _{CB} = 10 V, I _C = 0, f = 1.0 MHz)	C _{obo}	–	1.7	4.5	pF
Input Capacitance (V _{EB} = 0.5 V, I _C = 0, f = 1.0 MHz)	C _{ibo}	–	10	–	pF
Small – Signal Current Gain (I _C = 2.0 mA, V _{CE} = 5.0 V, f = 1.0 kHz)	h _{fe}	125 125 125 240 450	– – 220 330 600	500 900 260 500 900	–
Noise Figure (I _C = 0.2 mA, V _{CE} = 5.0 V, R _S = 2 kΩ, f = 1.0 kHz, Δf = 200 Hz)	NF	– – –	2.0 2.0 2.0	10 10 10	dB

1. I_B is value for which I_C = 11 mA at V_{CE} = 1.0 V.

BC547/BC548

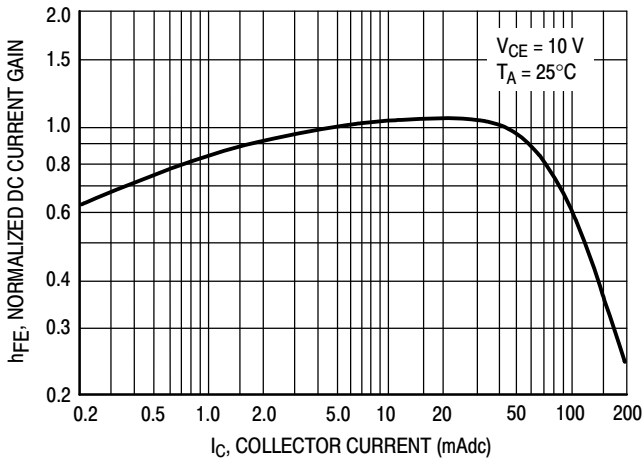


Figure 1. Normalized DC Current Gain

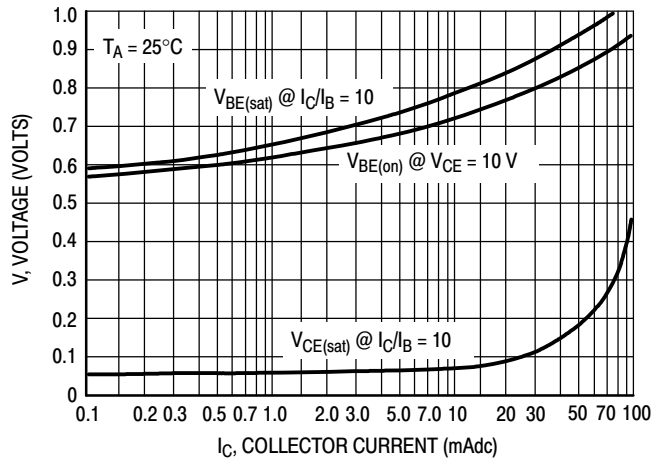


Figure 2. "Saturation" and "On" Voltages

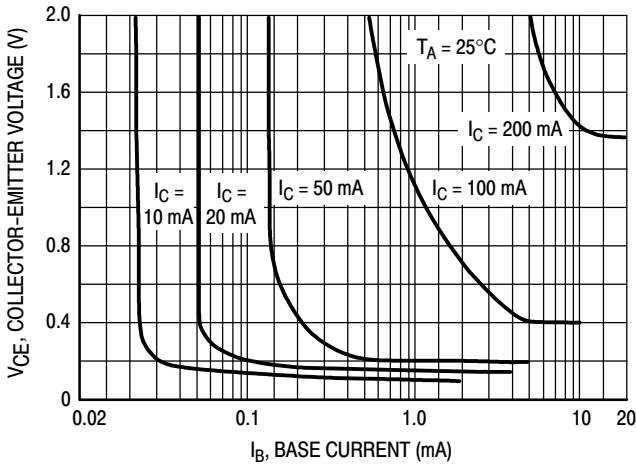


Figure 3. Collector Saturation Region

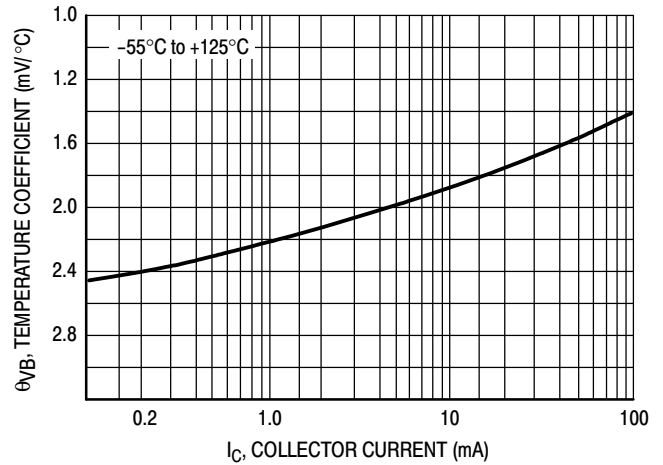


Figure 4. Base-Emitter Temperature Coefficient

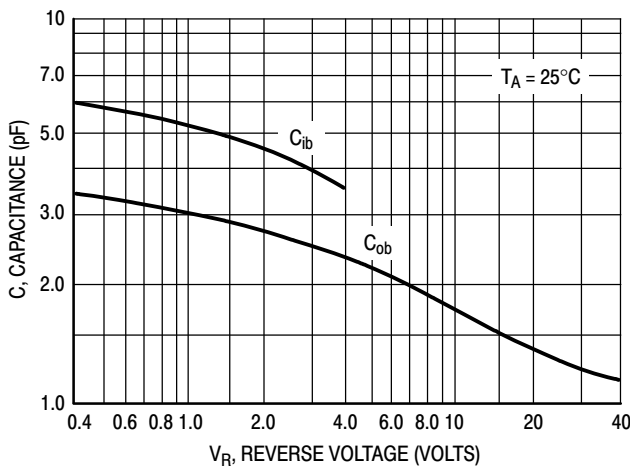


Figure 5. Capacitances

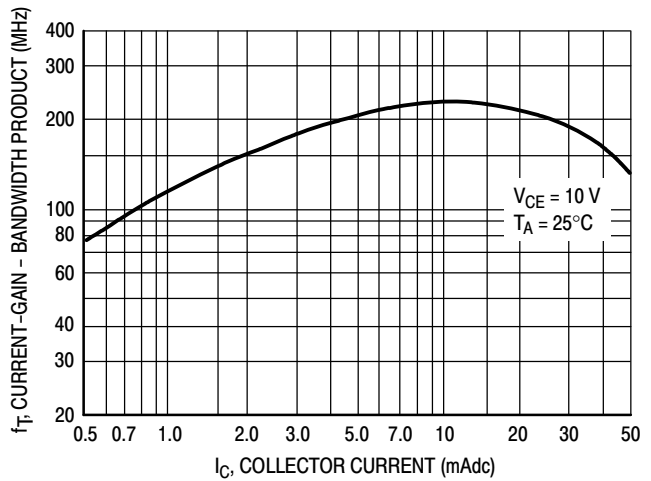


Figure 6. Current-Gain - Bandwidth Product

BC546



Figure 7. DC Current Gain



Figure 8. "On" Voltage



Figure 9. Collector Saturation Region



Figure 10. Base-Emitter Temperature Coefficient



Figure 11. Capacitance

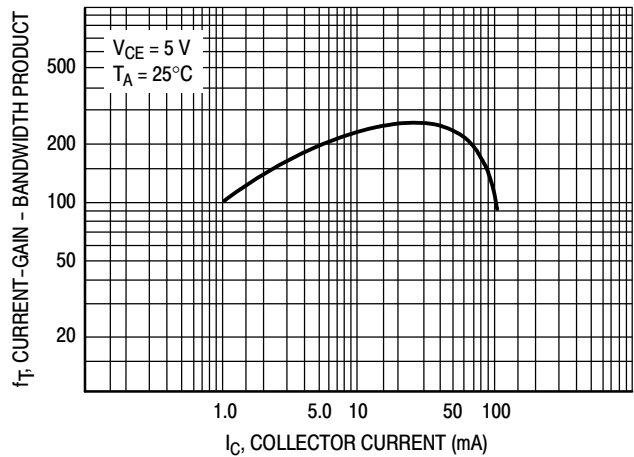


Figure 12. Current-Gain - Bandwidth Product

BC546B, BC547A, B, C, BC548B, C

ORDERING INFORMATION

Device	Package	Shipping†
BC546B	TO-92	5000 Units / Bulk
BC546BG	TO-92 (Pb-Free)	5000 Units / Bulk
BC546BRL1	TO-92	2000 / Tape & Reel
BC546BRL1G	TO-92 (Pb-Free)	2000 / Tape & Reel
BC546BZL1G	TO-92 (Pb-Free)	2000 / Ammo Box
BC547ARL	TO-92	2000 / Tape & Reel
BC547ARLG	TO-92 (Pb-Free)	2000 / Tape & Reel
BC547AZL1G	TO-92 (Pb-Free)	2000 / Ammo Box
BC547BG	TO-92 (Pb-Free)	5000 Units / Bulk
BC547BRL1G	TO-92 (Pb-Free)	2000 / Tape & Reel
BC547BZL1G	TO-92 (Pb-Free)	2000 / Ammo Box
BC547CG	TO-92 (Pb-Free)	5000 Units / Bulk
BC547CZL1G	TO-92 (Pb-Free)	2000 / Ammo Box
BC548BG	TO-92 (Pb-Free)	5000 Units / Bulk
BC548BRL1G	TO-92 (Pb-Free)	2000 / Tape & Reel
BC548BZL1G	TO-92 (Pb-Free)	2000 / Ammo Box
BC548CG	TO-92 (Pb-Free)	5000 Units / Bulk
BC548CZL1G	TO-92 (Pb-Free)	2000 / Ammo Box

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

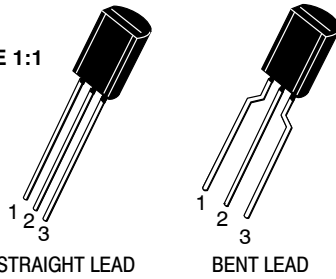
MECHANICAL CASE OUTLINE

PACKAGE DIMENSIONS

ON Semiconductor®

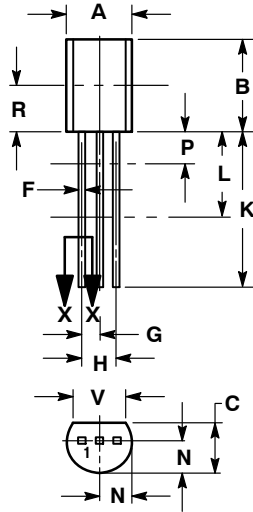


SCALE 1:1

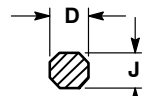


TO-92 (TO-226) 1 WATT
CASE 29-10
ISSUE A

DATE 08 MAY 2012



STRAIGHT LEAD

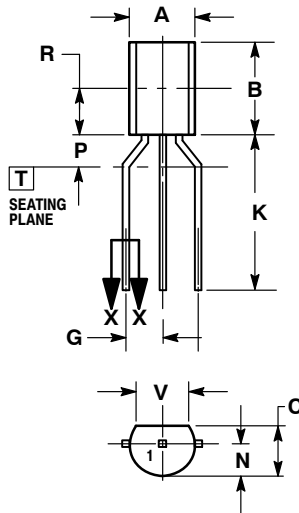


SECTION X-X

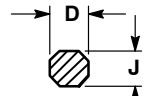
NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
4. DIMENSION F APPLIES BETWEEN DIMENSIONS P AND L. DIMENSIONS D AND J APPLY BETWEEN DIMENSIONS L AND K MINIMUM. THE LEAD DIMENSIONS ARE UNCONTROLLED IN DIMENSION P AND BEYOND DIMENSION K MINIMUM.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.175	0.205	4.44	5.21
B	0.290	0.310	7.37	7.87
C	0.125	0.165	3.18	4.19
D	0.018	0.021	0.46	0.53
F	0.016	0.019	0.41	0.48
G	0.045	0.055	1.15	1.39
H	0.095	0.105	2.42	2.66
J	0.018	0.024	0.46	0.61
K	0.500	---	12.70	---
L	0.250	---	6.35	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.135	---	3.43	---
V	0.135	---	3.43	---



BENT LEAD



SECTION X-X

NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED.
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B	0.290	0.310	7.37	7.87
C	0.125	0.165	3.18	4.19
D	0.018	0.021	0.46	0.53
G	0.094	0.102	2.40	2.80
J	0.018	0.024	0.46	0.61
K	0.500	---	12.70	---
N	0.080	0.105	2.04	2.66
P	---	0.100	---	2.54
R	0.135	---	3.43	---
V	0.135	---	3.43	---

STYLES ON PAGE 2

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CASE 29-10
ISSUE A**

DATE 08 MAY 2012

STYLE 1:
PIN 1. EMITTER
2. BASE
3. COLLECTOR

STYLE 2:
PIN 1. BASE
2. EMITTER
3. COLLECTOR

STYLE 3:
PIN 1. ANODE
2. ANODE
3. CATHODE

STYLE 4:
PIN 1. CATHODE
2. CATHODE
3. ANODE

STYLE 5:
PIN 1. DRAIN
2. SOURCE
3. GATE

STYLE 6:
PIN 1. GATE
2. SOURCE & SUBSTRATE
3. DRAIN

STYLE 7:
PIN 1. SOURCE
2. DRAIN
3. GATE

STYLE 8:
PIN 1. DRAIN
2. GATE
3. SOURCE & SUBSTRATE

STYLE 9:
PIN 1. BASE 1
2. EMITTER
3. BASE 2

STYLE 10:
PIN 1. CATHODE
2. GATE
3. ANODE

STYLE 11:
PIN 1. ANODE
2. CATHODE & ANODE
3. CATHODE

STYLE 12:
PIN 1. MAIN TERMINAL 1
2. GATE
3. MAIN TERMINAL 2

STYLE 13:
PIN 1. ANODE 1
2. GATE
3. CATHODE 2

STYLE 14:
PIN 1. EMITTER
2. COLLECTOR
3. BASE

STYLE 15:
PIN 1. ANODE 1
2. CATHODE
3. ANODE 2

STYLE 16:
PIN 1. ANODE
2. GATE
3. CATHODE

STYLE 17:
PIN 1. COLLECTOR
2. BASE
3. EMITTER

STYLE 18:
PIN 1. ANODE
2. CATHODE
3. NOT CONNECTED

STYLE 19:
PIN 1. GATE
2. ANODE
3. CATHODE

STYLE 20:
PIN 1. NOT CONNECTED
2. CATHODE
3. ANODE

STYLE 21:
PIN 1. COLLECTOR
2. EMITTER
3. BASE

STYLE 22:
PIN 1. SOURCE
2. GATE
3. DRAIN

STYLE 23:
PIN 1. GATE
2. SOURCE
3. DRAIN

STYLE 24:
PIN 1. EMITTER
2. COLLECTOR/ANODE
3. CATHODE

STYLE 25:
PIN 1. MT 1
2. GATE
3. MT 2

STYLE 26:
PIN 1. V_{CC}
2. GROUND 2
3. OUTPUT

STYLE 27:
PIN 1. MT
2. SUBSTRATE
3. MT

STYLE 28:
PIN 1. CATHODE
2. ANODE
3. GATE

STYLE 29:
PIN 1. NOT CONNECTED
2. ANODE
3. CATHODE

STYLE 30:
PIN 1. DRAIN
2. GATE
3. SOURCE

STYLE 31:
PIN 1. GATE
2. DRAIN
3. SOURCE


STYLE 32:
PIN 1. BASE
2. COLLECTOR
3. EMITTER

STYLE 33:
PIN 1. RETURN
2. INPUT
3. OUTPUT

STYLE 34:
PIN 1. INPUT
2. GROUND
3. LOGIC

STYLE 35:
PIN 1. GATE
2. COLLECTOR
3. EMITTER

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